**Product data sheet** 

# 1. Product profile

### 1.1 General description

P-channel enhancement mode Field-Effect Transistor (FET) in a leadless medium power DFN2020MD-6 (SOT1220) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

### 1.2 Features and benefits

- Trench MOSFET technology
- Small and leadless ultra thin SMD plastic package: 2 x 2 x 0.65 mm
- Exposed drain pad for excellent thermal conduction
- Tin-plated 100 % solderable side pads for optical solder inspection

### 1.3 Applications

- Charging switch for portable devices
- DC-to-DC converters
- Power management in battery-driven portable devices
- Hard disk and computing power management

#### 1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> = 25 °C		-	-	-20	V
$V_{GS}$	gate-source voltage			-12	-	12	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = -4.5 V; T <sub>amb</sub> = 25 °C; t ≤ 5 s	[1]	-	-	-7.9	Α
Static characteristics							
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS}$ = -4.5 V; $I_D$ = -5.5 A; $T_j$ = 25 °C		-	30	37	mΩ

<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.



20 V, single P-channel Trench MOSFET

# 2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	D	drain	1 6	D
2	D	drain	7 7	
3	G	gate	2 5	G T T
4	S	source	3 8 4	\$ 017aaa257
5	D	drain	Transparent top view	
6	D	drain	DFN2020MD-6 (SOT1220)	
7	D	drain		
8	S	source		

# 3. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
PMPB33XP	DFN2020MD-6	plastic thermal enhanced ultra thin small outline package; no leads; 6 terminals	SOT1220			

# 4. Marking

Table 4. Marking codes

Type number	Marking code
PMPB33XP	18

# 5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
$V_{DS}$	drain-source voltage	T <sub>j</sub> = 25 °C		-	-20	V
V <sub>GS</sub>	gate-source voltage			-12	12	V
I <sub>D</sub>	drain current	$V_{GS} = -4.5 \text{ V}; T_{amb} = 25 \text{ °C}; t \le 5 \text{ s}$	[1]	-	-7.9	Α
		$V_{GS}$ = -4.5 V; $T_{amb}$ = 25 °C	[1]	-	-5.5	Α
		$V_{GS}$ = -4.5 V; $T_{amb}$ = 100 °C	[1]	-	-3.5	Α
I <sub>DM</sub>	peak drain current	$T_{amb}$ = 25 °C; single pulse; $t_p \le 10 \mu s$		-	-22	Α
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = 25 °C	[1]	-	1.7	W
DMDD22VD	AII :-4-					

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Symbol	Parameter	Conditions		Min	Max	Unit
		T <sub>amb</sub> = 25 °C; t ≤ 5 s	[1]	-	3.5	W
		T <sub>sp</sub> = 25 °C		-	12.5	W
Tj	junction temperature			-55	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C
Source-dra	in diode					
I <sub>S</sub>	source current	T <sub>amb</sub> = 25 °C	[1]	-	-1.9	Α

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.

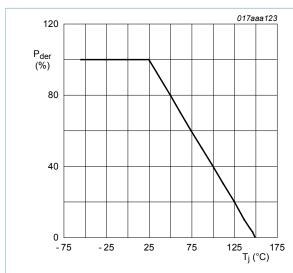


Fig. 1. Normalized total power dissipation as a function of junction temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

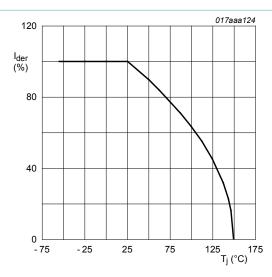


Fig. 2. Normalized continuous drain current as a function of junction temperature

$$I_{der} = \frac{I_D}{I_{D(25^{\circ}\text{C})}} \times 100 \%$$

# 20 V, single P-channel Trench MOSFET

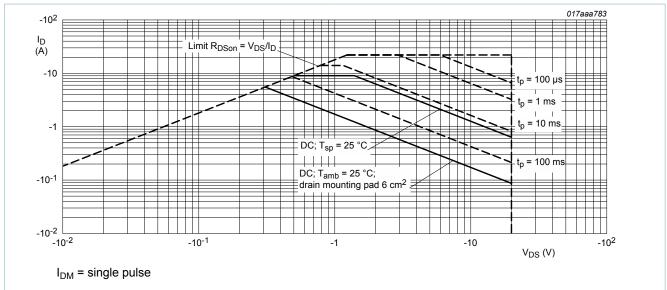


Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

# 6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R <sub>th(j-a)</sub> thermal resistant from junction to ambient	thermal resistance		[1]	-	235	270	K/W
	•		<u>[2]</u>	-	67	74	K/W
	ambient	in free air; t ≤ 5 s	<u>[2]</u>	-	33	36	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point			-	5	10	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.

4/14

20 V, single P-channel Trench MOSFET

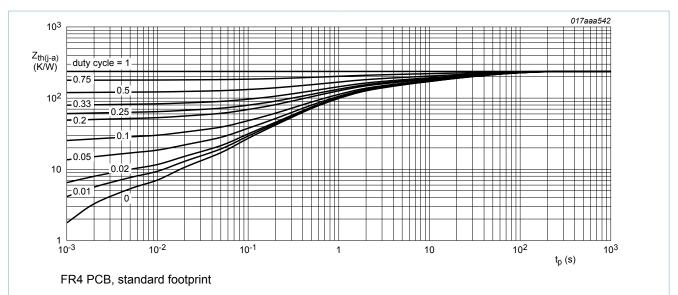


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

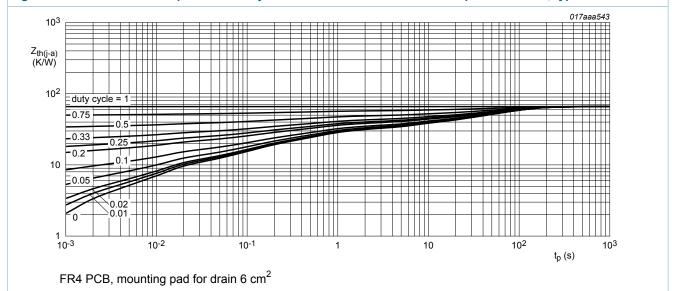


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

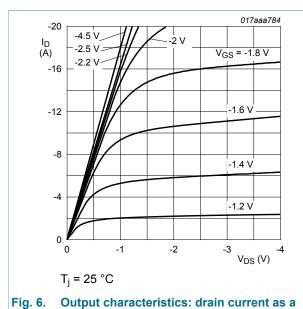
# 7. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Static chara	Static characteristics						
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = -250 \mu A; V_{GS} = 0 V; T_j = 25 °C$		-20	-	-	V
$V_{GSth}$	gate-source threshold voltage	$I_D$ = -250 $\mu$ A; $V_{DS}$ = $V_{GS}$ ; $T_j$ = 25 °C		-0.47	-0.68	-0.9	V
I <sub>DSS</sub>	drain leakage current	$V_{DS}$ = -20 V; $V_{GS}$ = 0 V; $T_j$ = 25 °C		-	-	-1	μA
I <sub>GSS</sub>	gate leakage current	$V_{GS} = -12 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$		-	-	-100	nA
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Symbol	Parameter	Conditions		Min	Тур	Max	Unit
		V <sub>GS</sub> = 12 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C		-	-	100	nA
R <sub>DSon</sub>	drain-source on-state	$V_{GS}$ = -4.5 V; $I_{D}$ = -5.5 A; $T_{j}$ = 25 °C		-	30	37	mΩ
	resistance	$V_{GS}$ = -4.5 V; $I_D$ = -5.5 A; $T_j$ = 150 °C		-	45	56	mΩ
		$V_{GS}$ = -2.5 V; $I_{D}$ = -5 A; $T_{j}$ = 25 °C		-	35	46	mΩ
		$V_{GS}$ = -1.8 V; $I_D$ = -2.1 A; $T_j$ = 25 °C		-	45	65	mΩ
9 <sub>fs</sub>	forward transconductance	$V_{DS}$ = -10 V; $I_{D}$ = -5.5 A; $T_{j}$ = 25 °C		-	28	-	S
$R_G$	gate resistance	f = 1 MHz		-	4.5	-	Ω
Dynamic ch	naracteristics		1	1			,
Q <sub>G(tot)</sub>	total gate charge	$V_{DS}$ = -10 V; $I_{D}$ = -5.5 A; $V_{GS}$ = -4.5 V;		-	15	23	nC
Q <sub>GS</sub>	gate-source charge	T <sub>j</sub> = 25 °C		-	2	-	nC
$Q_{GD}$	gate-drain charge			-	4	-	nC
C <sub>iss</sub>	input capacitance	V <sub>DS</sub> = -10 V; f = 1 MHz; V <sub>GS</sub> = 0 V;		-	1575	-	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C		-	145	-	pF
C <sub>rss</sub>	reverse transfer capacitance			-	125	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS}$ = -10 V; $I_{D}$ = -5.5 A; $V_{GS}$ = -4.5 V;		-	12	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 ^{\circ}C$		-	42	-	ns
t <sub>d(off)</sub>	turn-off delay time			-	62	-	ns
t <sub>f</sub>	fall time			-	23	-	ns
Source-dra	in diode		1	1			
V <sub>SD</sub>	source-drain voltage	I <sub>S</sub> = -1.9 A; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C		-	-0.6	-1.2	V



function of drain-source voltage; typical values

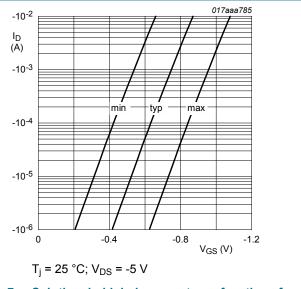


Fig. 7. Sub-threshold drain current as a function of gate-source voltage

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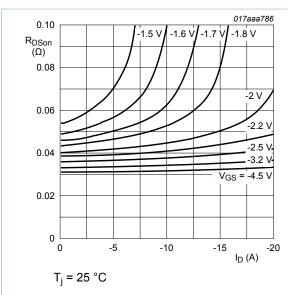


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

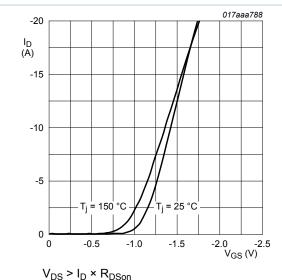


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

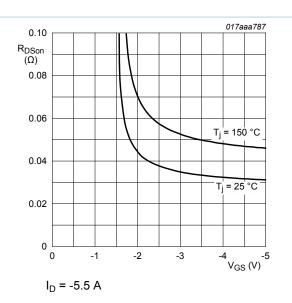


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

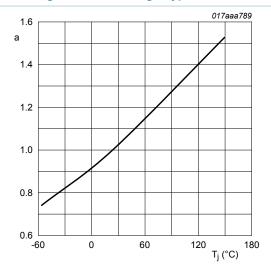


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$

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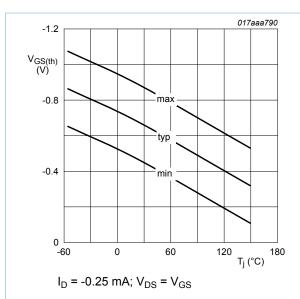


Fig. 12. Gate-source threshold voltage as a function of junction temperature

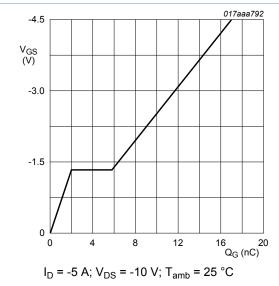
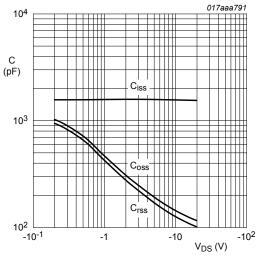


Fig. 14. Gate-source voltage as a function of gate charge; typical values



 $f = 1 MHz; V_{GS} = 0 V$ 

Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

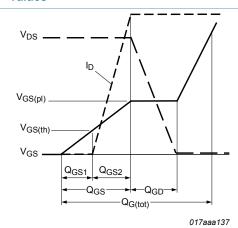
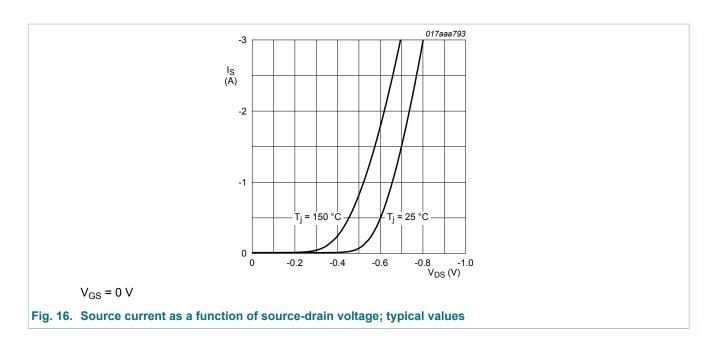
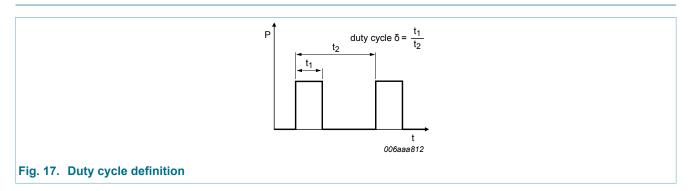


Fig. 15. Gate charge waveform definitions

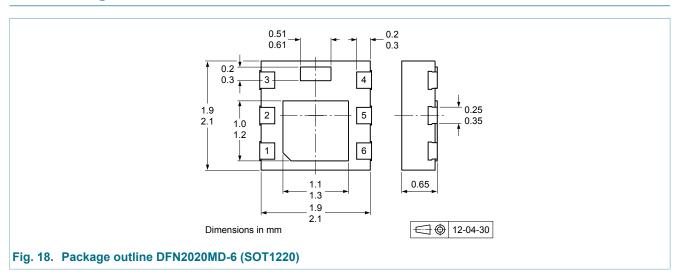
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# 8. Test information



# 9. Package outline

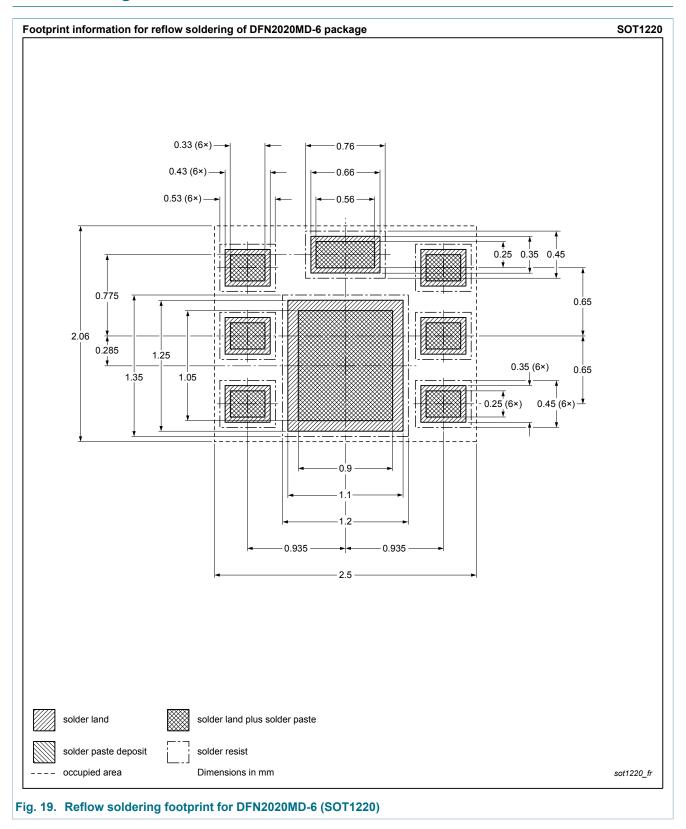


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# 10. Soldering



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# 11. Revision history

### Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMPB33XP v.1	20120905	Product data sheet	-	-

#### 20 V, single P-channel Trench MOSFET

# 12. Legal information

#### 12.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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# 20 V, single P-channel Trench MOSFET

# 13. Contents

1	Product profile	1
1.1	General description	1
1.2	Features and benefits	1
1.3	Applications	1
1.4	Quick reference data	1
2	Pinning information	2
3	Ordering information	2
4	Marking	2
5	Limiting values	2
6	Thermal characteristics	4
7	Characteristics	5
8	Test information	9
9	Package outline	9
10	Soldering	
11	Revision history	11
12	Legal information	
12.1	Data sheet status	12
12.2	Definitions	12
12.3	Disclaimers	12
12.4	Trademarks	13

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